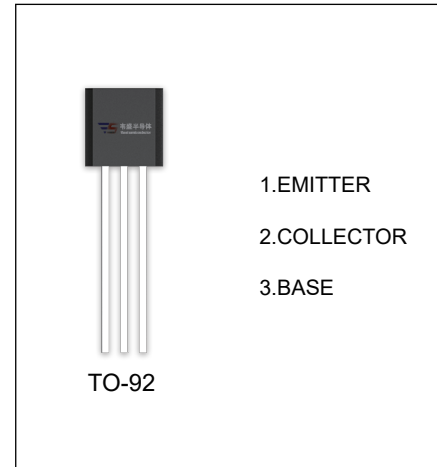


MPSA17 TRANSISTOR (NPN)

FEATURES

- High $V_{(BR)EBO}$: 12V



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
MPSA17	TO-92	Bulk	1000pcs/Bag
MPSA17-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CEO}	Collector-Ease Voltage	40	V
V_{EBO}	Emitter-Base Voltage	12	V
I_C	Collector Current -Continuous	0.1	A
P_C	Collector Power Dissipation	300	mW
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55 to +150	$^{\circ}\text{C}$

T_a=25 °C unless otherwise specified

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 1mA, I _E =0	40		V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 100μA, I _C =0	12		V
Collector cut-off current	I _{CBO}	V _{CB} =30V, I _E =0		0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =10V, I _C =0		0.1	μA
DC current gain	h _{FE}	V _{CE} =10V, I _C =5mA	200	800	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 10mA, I _B =1mA		0.25	V
Transition frequency	f _T	V _{CE} =10V, I _C =5mA, f=100MHz	80		MHz
Collector output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz		4	pF